



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ C$
60V	$5\Omega @ V_{GS} = 10V$	210mA
	$7.5\Omega @ V_{GS} = 5V$	170mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package

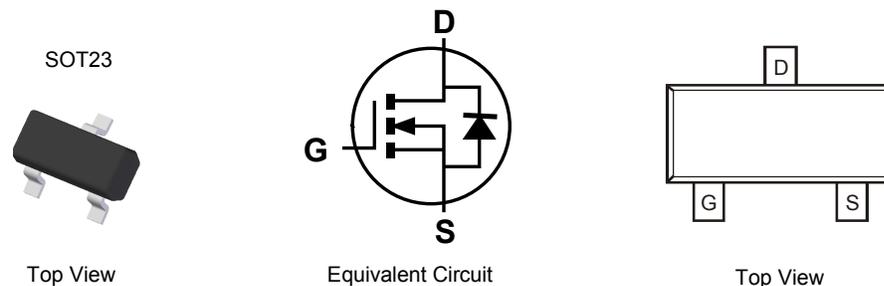
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$			V_{DGR}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Pulsed				± 40	
Continuous Drain Current (Note 5) $V_{GS} = 10V$	Steady State	$T_A = +25^\circ\text{C}$	I_D	170	mA
		$T_A = +85^\circ\text{C}$		120	
		$T_A = +100^\circ\text{C}$		105	
Continuous Drain Current (Note 6) $V_{GS} = 10V$	Steady State	$T_A = +25^\circ\text{C}$	I_D	210	mA
		$T_A = +85^\circ\text{C}$		150	
		$T_A = +100^\circ\text{C}$		135	
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.2	A
Continuous Pulsed				0.5	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	800	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	P_D	370	mW
	(Note 6)		540	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	348	$^\circ\text{C/W}$
	(Note 6)		241	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	91	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$ @ $T_J = +25^\circ\text{C}$ @ $T_J = +125^\circ\text{C}$
Gate-Body Leakage	I_{GSS}	—	—	± 10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
		—	2.4	5.0		$V_{GS} = 10V, I_D = 0.5A$
		—	4.4	13.5		$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	g_{FS}	80	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}	—	0.78	1.5	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	22	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.0	5.0	pF	
Gate Resistance	R_g	—	120	—	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ $f = 1.0MHz$
Total Gate Charge ($V_{GS} = 4.5V$)	Q_g	—	223	—	pC	$V_{DS} = 10V, I_D = 250mA$
Gate-Source Charge	Q_{gs}	—	82	—		
Gate-Drain Charge	Q_{gd}	—	178	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.8	—	ns	$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega$
Turn-On Rise Time	t_R	—	3.0	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	7.6	—		
Turn-Off Fall Time	t_F	—	5.6	—		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

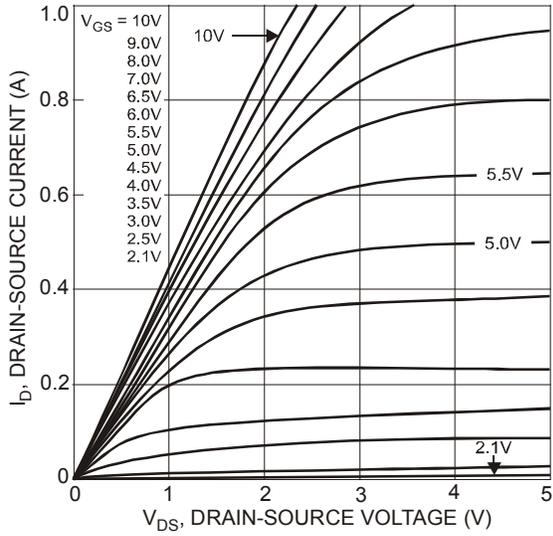


Fig. 1 On-Region Characteristics

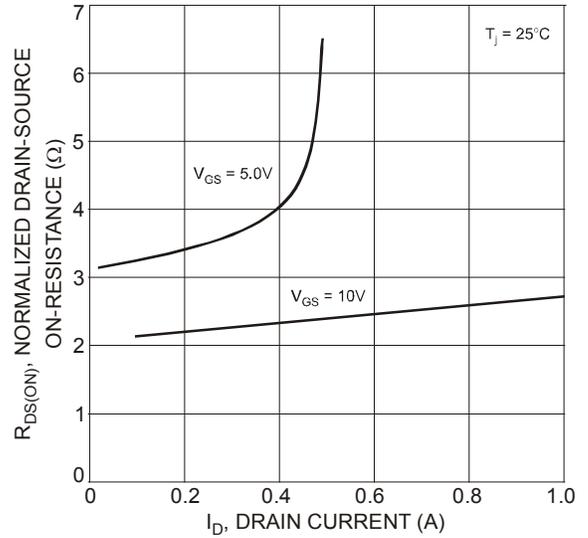


Fig. 2 On-Resistance vs. Drain Current

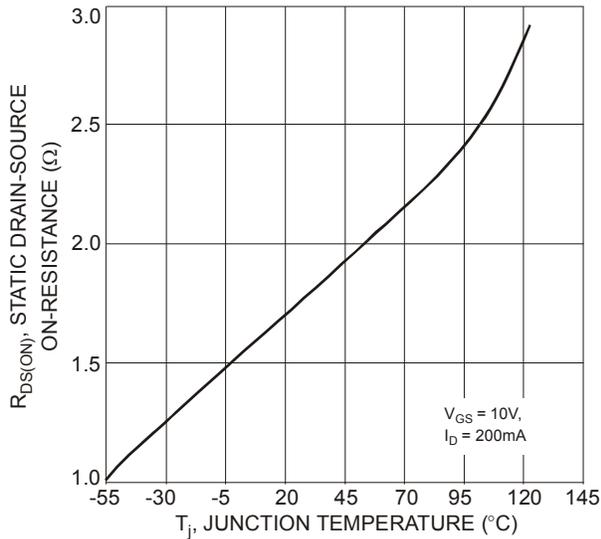


Fig. 3 On-Resistance vs. Junction Temperature

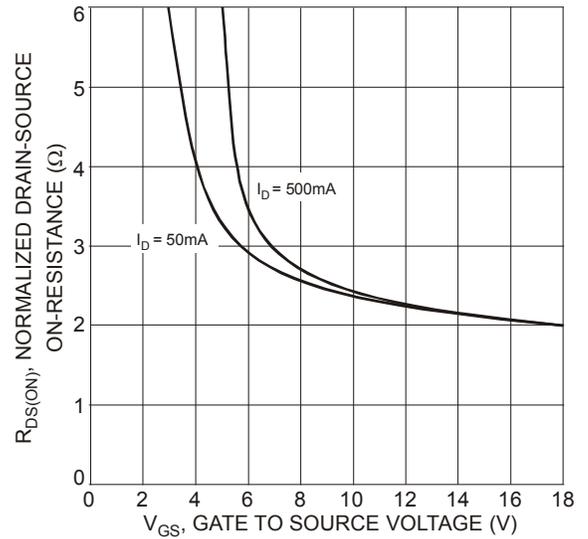


Fig. 4 On-Resistance vs. Gate-Source Voltage

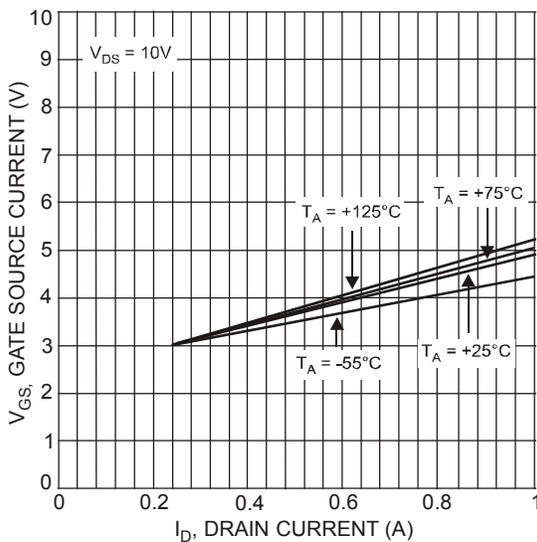


Fig. 5 Typical Transfer Characteristics

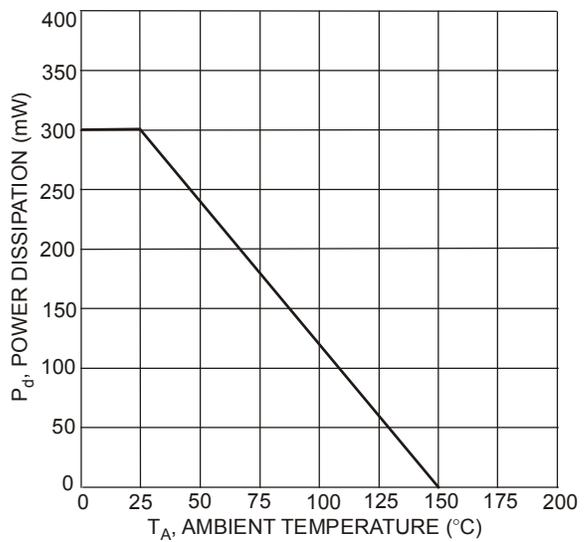
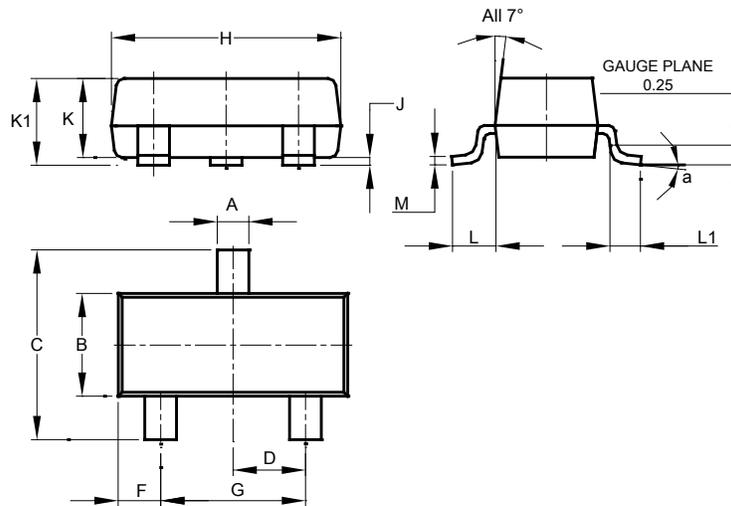


Fig. 6 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

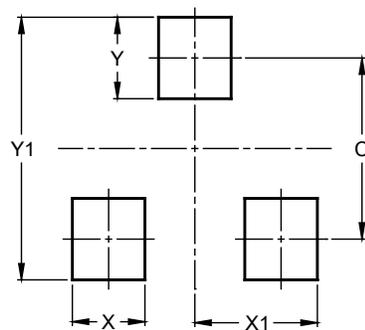
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9